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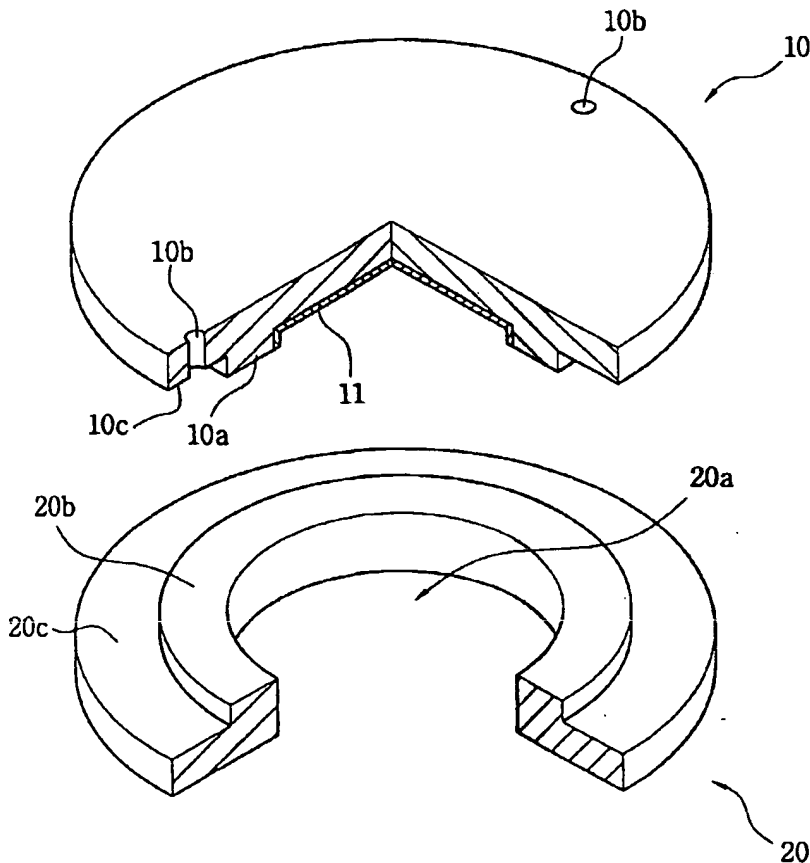
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(54) Title: **ELECTRODE FOR DRY ETCHING A WAFER**



(57) Abstract: Disclosed is an electrode for dry etching a wafer. The electrode includes a first electrode and a second electrode. The first electrode includes a first flat plate and a ring-shaped first protrusion corresponding to one surface of the edge of a wafer, and the second electrode includes a second flat plate and a ring-shaped second protrusion corresponding to the other surface of the edge of the wafer. The first plate and the second flat plate are the same dimension, and the first protrusion and the second protrusion are the same dimension.

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